ECEE 434 Lab#3 - Logic Gates

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Introduction & Background



Procedure

The goal of this lab is to have the rising and falling propagation delays be equivalent. Since we are adjusting the size of the transistors for this design requirement to be true, the most straightforward way of calculating them is using the propagation time equations.

$$t_{PHL} = 0.69 * R_n * C_{load}$$

$$t_{PLH} = 0.69 * R_p * C_{load}$$

Based off of these equations, the only unknowns are the resistance values for the transistors, R_N and R_N .

$$R_N = \frac{12.5}{(W/L)_n}$$

$$R_P = \frac{30}{(W/L)_p}$$

Each circuit had its own worst case scenario that affected the equivalent resistances of the pull up and pull down networks.



NAND Gate

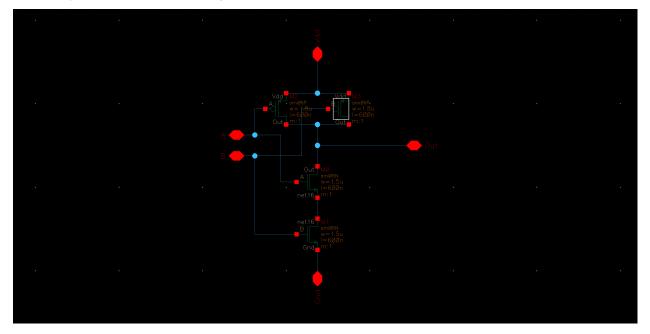
For the NAND gate (Fig. 1) the worst case scenario was when only one PMOS transistor was on, and two NMOS transistors were on. Thus, in order for both networks to have equivalent propagation delays and equivalents resistances, the equivalent resistances of the pull up and pull down worst case networks had to be set to each other, as opposed to the best case scenario resistances. For the NAND circuit, this would be:

$$R_P = 2R_N$$

After setting R_n equal to R_p so that the t_{PLH} and t_{PHL} values would be equivalent, the ratio of p to n for the NAND gate was:

$$p = 1.2n$$

Since the default width for the transistors in Cadence is $1.5\mu m$, that value was chosen for the n-type transistor, and then p was calculated to be $1.8\mu m$.





NOR Gate

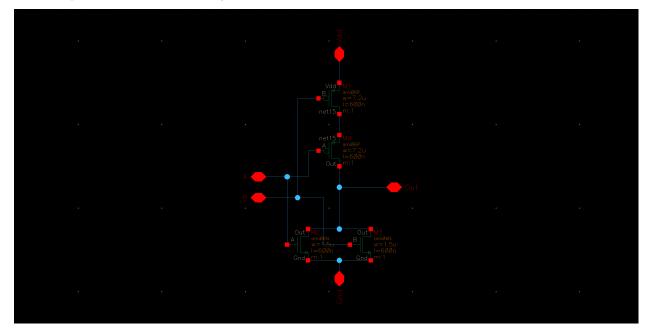
For the NOR gate (Fig. 2), the worst case scenario was when two PMOS transistors were on, and one NMOS transistor was on. When the equivalent resistances were set to eachother, the resultant equation was as follows:

$$2R_P = R_N$$

After setting R_n equal to R_p so that the t_{PLH} and t_{PHL} values would be equivalent, the ratio of p to n for the NOR gate was:

$$p = 4.8n$$

Since the default width for the transistors in Cadence is $1.5\mu m$, that value was chosen for the n-type transistor, and then p was calculated to be $7.2\mu m$.





XOR Gate

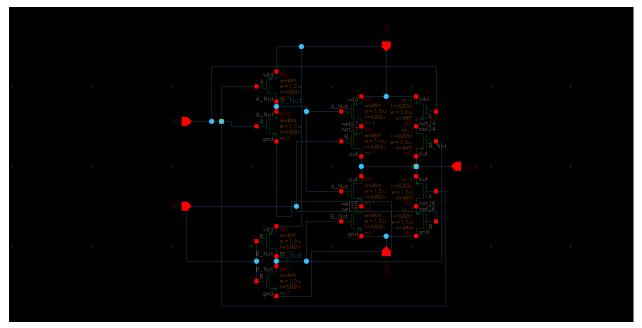
The worst case scenario for the XOR gate (Fig. 3) is similar to that of the inverter, where the number of transistors in the pull up network were equivalent to the number of transistors in the pulldown network. When the equivalent resistances were set to eachother, the resultant equation was as follows:

$$2R_P = 2R_N$$

Which can be simplified to $2R_P = 2R_N$. After setting R_n equal to R_p so that the t_{PLH} and t_{PHL} values would be equivalent, the ratio of p to n for the NOR gate was:

$$p = 3.6n$$

Since the default width for the transistors in Cadence is $1.5\mu m$, that value was chosen for the n-type transistor, and then p was calculated to be $3.6\mu m$.





Results



Conclusion

